

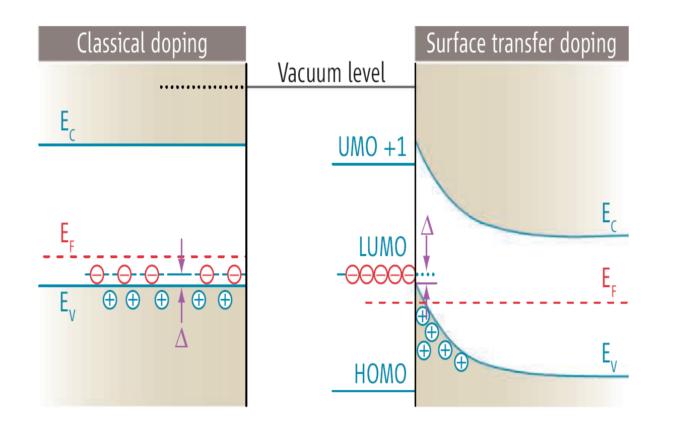


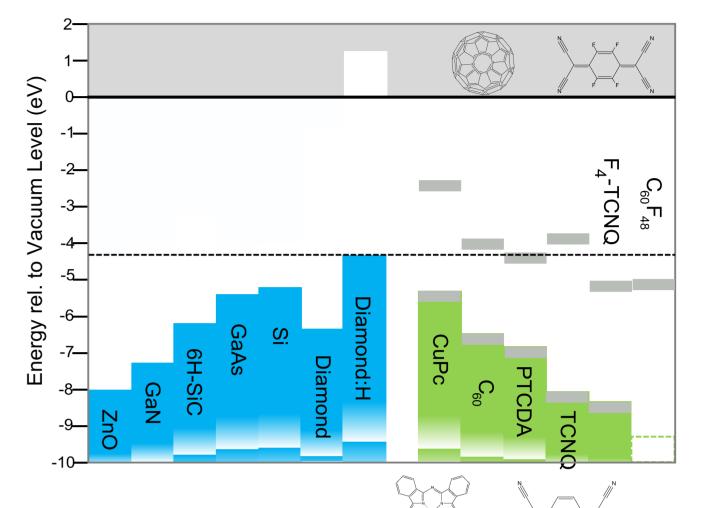
Surface Transfer Doping of Diamond (100) by Organic Molecules

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Introduction

Despite of numerous exceptional electronic and properties diamond, mechanical of the development of diamond-based electronic devices is severely hampered by a number of setbacks of conventional doping of diamond such as high dopant activation energy and processing difficulties. Surface transfer doping, achieved by electron exchange which is semiconductor to its surface а between adsorbates, is highly promising to tackle this challenge.





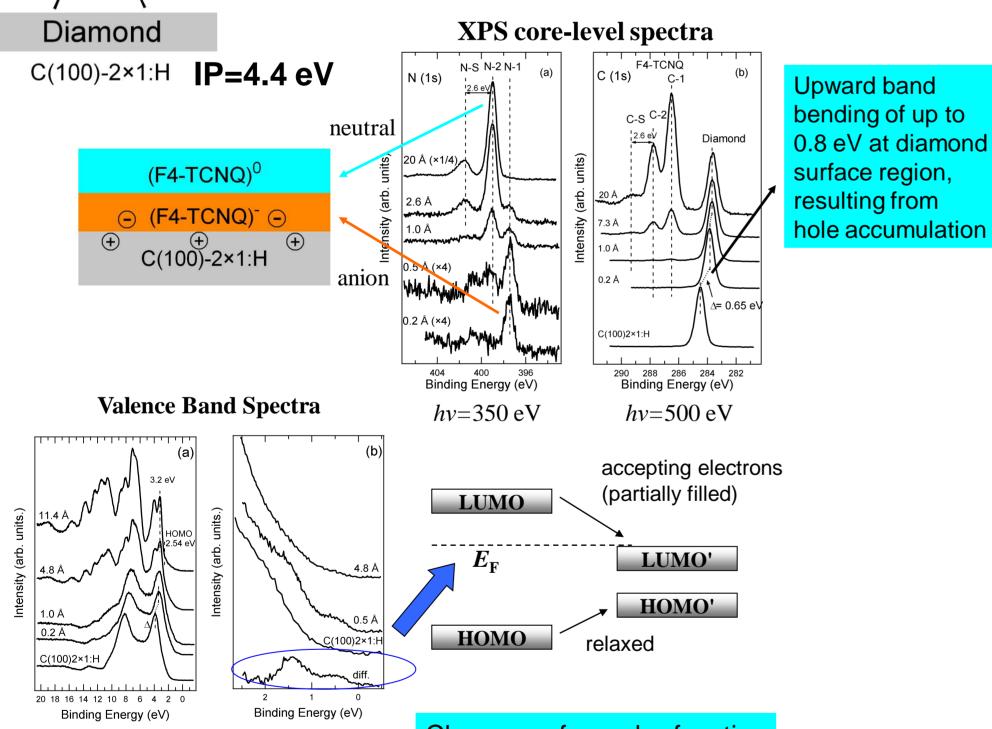
Results and Discussions



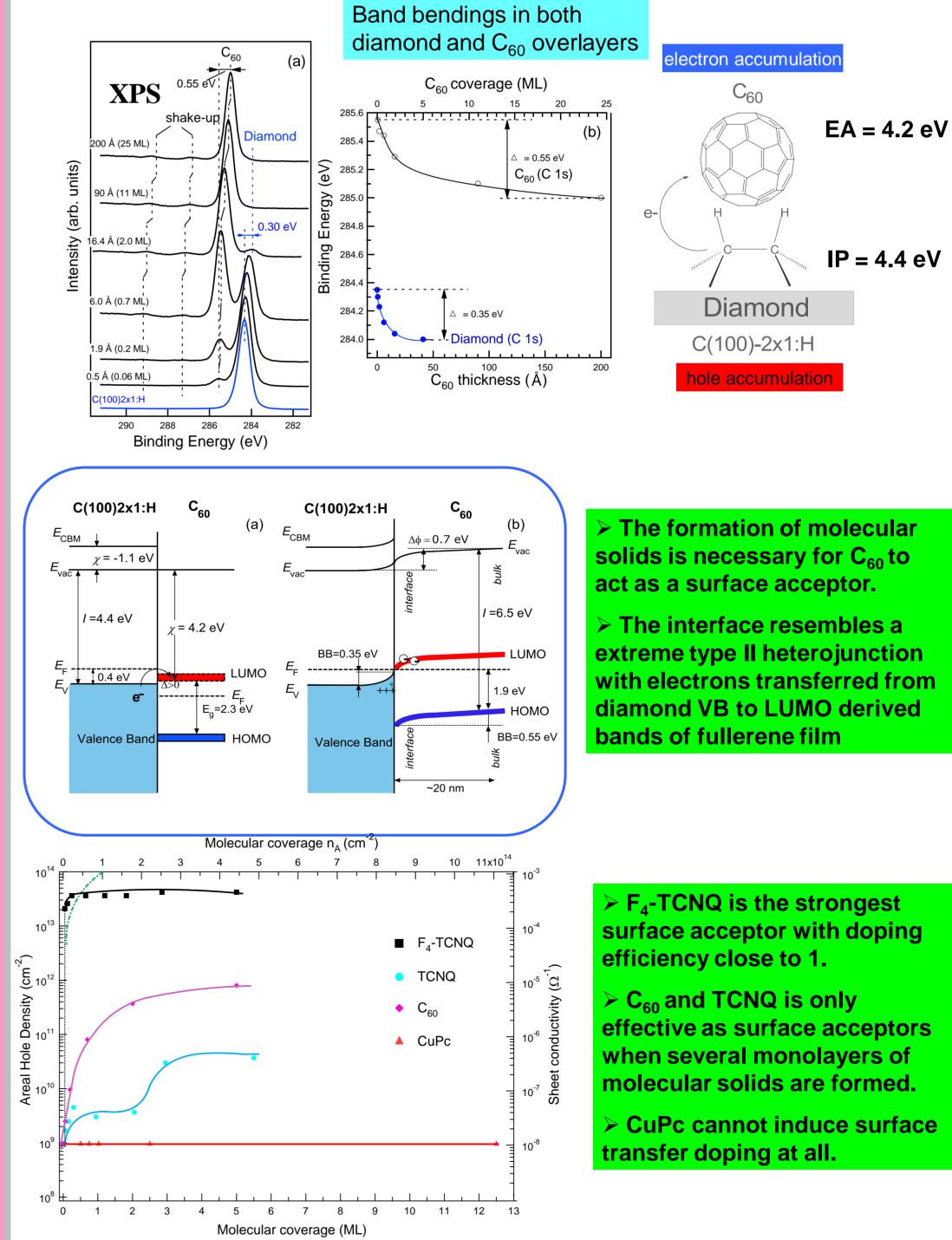
F4-TCNQ EA=5.24 eV

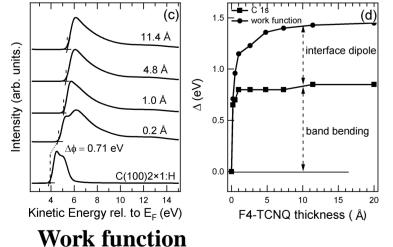
Favoring electron transfer from E_{V} of diamond to LUMO of F₄-TCNQ:

A excellent test bed for surface transfer doping

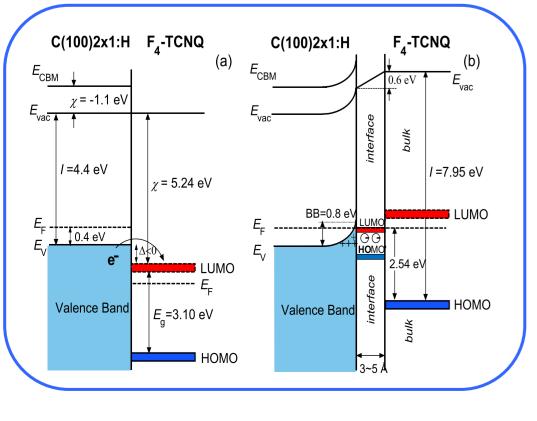


II: C₆₀





of work function Change with F₄-TCNQ deposition results from band bending interface dipole and formation



 \succ F₄-TCNQ can already induce significant p-type surface transfer doping of diamond even in molecular form.

Electrons are transferred from diamond valence band to molecular LUMOs.

Diamond becomes degenerate at the surface.

Conclusions

• Controllable *p*-type surface transfer doping of diamond by organic molecules is unambiguously demonstrated through PES.

◆ The different doping efficiencies of tested molecules are related with their varied electron affinities.

• Surface transfer doping is a versatile scheme that can be applied to other semiconductor systems.